

N-channel 100V 13.9mΩ standard level MOSFET in TO220. 10 August 2012 Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in TO220 package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Improved dynamic avalanche performance
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switching
- Motor control
- Server power supplies

1.4 Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------|----------------------------------|---|-----|-----|------|------|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | - | 100 | V |
| I _D | drain current | T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u> | [1] | - | - | 68 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | | - | - | 170 | W |
| Tj | junction temperature | | | -55 | - | 175 | °C |
| Static chara | acteristics | | I | | | | |
| R _{DSon} | drain-source on-state resistance | V_{GS} = 10 V; I _D = 15 A; T _j = 100 °C; Fig. 12 | | - | 19.4 | 25 | mΩ |
| | | V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 13 | [2] | - | 10.8 | 13.9 | mΩ |
| Dynamic ch | naracteristics | 1 | ı | 1 | 1 | | |
| Q_{GD} | gate-drain charge | V_{GS} = 10 V; I _D = 25 A; V _{DS} = 50 V; Fig. 15; Fig. 14 | | - | 17 | - | nC |

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| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------------|---|--|--|-----|-----|-----|------|
| Q _{G(tot)} | total gate charge | V _{GS} = 10 V; I _D = 25 A; V _{DS} = 50 V; <u>Fig. 14; Fig. 15</u> | | - | 59 | - | nC |
| Avalanche ruggedness | | | | | | | |
| E _{DS(AL)S} | non-repetitive drain- source avalanche energy | $\label{eq:VGS} \begin{array}{l} V_{GS} \texttt{=} 10 \; V; \; T_{j(\text{init})} \texttt{=} 25 \; ^{\circ}\text{C}; \; I_{D} \texttt{=} 68 \; A; \\ V_{sup} \texttt{\leq} 100 \; V; \; \text{unclamped}; \; R_{GS} \texttt{=} 50 \; \Omega \end{array}$ | | - | - | 128 | mJ |

Continuous current is limited by package Measured 3 mm from package. [1]

[2]

2. **Pinning information**

| D | 0 | Description of the second s | | |
|-----|--------|---|--------------------|---|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | G | gate | mb | D |
| 2 | D | drain | | |
| 3 | S | source | | G - U - T - T - T - T - T - T - T - T - T |
| mb | D | mounting base; connected to drain | | mbb076 S |
| | | | TO-220AB (SOT78) | |

Ordering information 3.

| Table 3. Ordering int | formation | | | | | |
|-----------------------|-----------|--|---------|--|--|--|
| Type number | Package | Package | | | | |
| | Name | Description | Version | | | |
| PSMN013-100PS | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78 | | | |

Marking 4.

| Table 4. Marking codes | |
|------------------------|---------------|
| Type number | Marking code |
| PSMN013-100PS | PSMN013-100PS |

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5. Limiting values

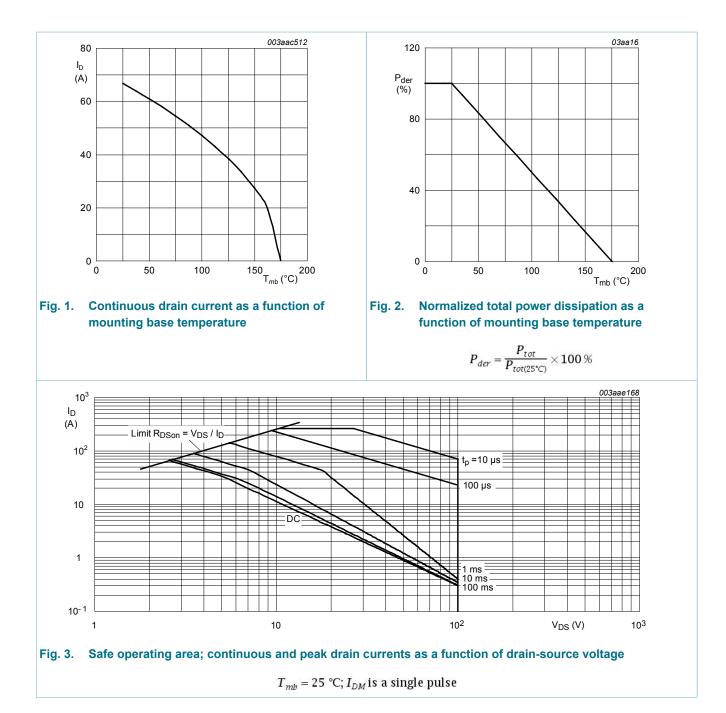
Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|--|--|-----|-----|-----|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | 100 | V |
| V _{DGR} | drain-gate voltage | $T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$ | | - | 100 | V |
| V _{GS} | gate-source voltage | | | -20 | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u> | [1] | - | 47 | Α |
| | | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u> | [1] | - | 68 | Α |
| I _{DM} | peak drain current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3 | | - | 272 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | | - | 170 | W |
| T _{stg} | storage temperature | | | -55 | 175 | °C |
| Tj | junction temperature | | | -55 | 175 | °C |
| T _{sld(M)} | peak soldering temperature | | | - | 260 | °C |
| Source-drai | in diode | | | | | |
| I _S | source current | T _{mb} = 25 °C | [1] | - | 68 | А |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | | - | 272 | Α |
| Avalanche | ruggedness | · | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | V_{GS} = 10 V; T _{j(init)} = 25 °C; I _D = 68 A; V _{sup} ≤ 100 V; unclamped; R _{GS} = 50 Ω | | - | 128 | mJ |

[1] Continuous current is limited by package

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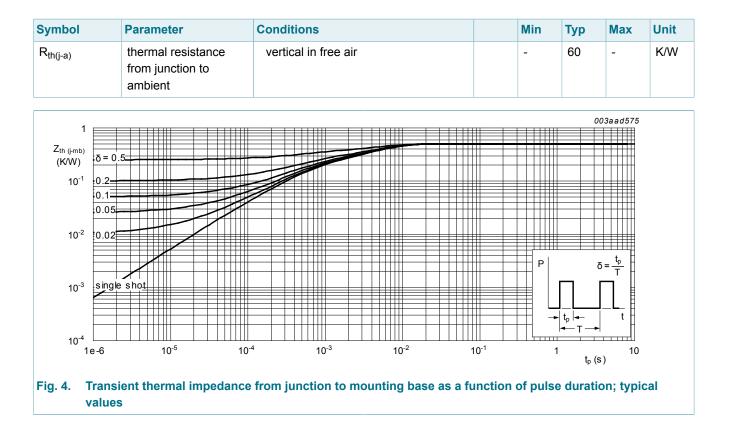
6. Thermal characteristics

| Table 6. The | rmal characteristics | | | | | |
|-----------------------|---|------------|-----|-----|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. 4 | - | 0.5 | 0.9 | K/W |

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7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|----------------------------------|--|-----|------|-----|------|
| Static chara | acteristics | · · · · | | | | |
| V _{(BR)DSS} | drain-source | I _D = 0.25 mA; V _{GS} = 0 V; T _j = -55 °C | 90 | - | - | V |
| | breakdown voltage | I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C | 100 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10 | 1 | - | - | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 10; Fig. 11 | 2 | 3 | 4 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10 | - | - | 4.6 | V |
| I _{DSS} | drain leakage current | V_{DS} = 100 V; V_{GS} = 0 V; T_j = 125 °C | - | - | 100 | μA |
| | | V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C | - | 0.06 | 2 | μA |
| I _{GSS} | gate leakage current | V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C | - | 10 | 100 | nA |
| | | V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C | - | 10 | 100 | nA |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; Fig. 12 | - | 19.4 | 25 | mΩ |

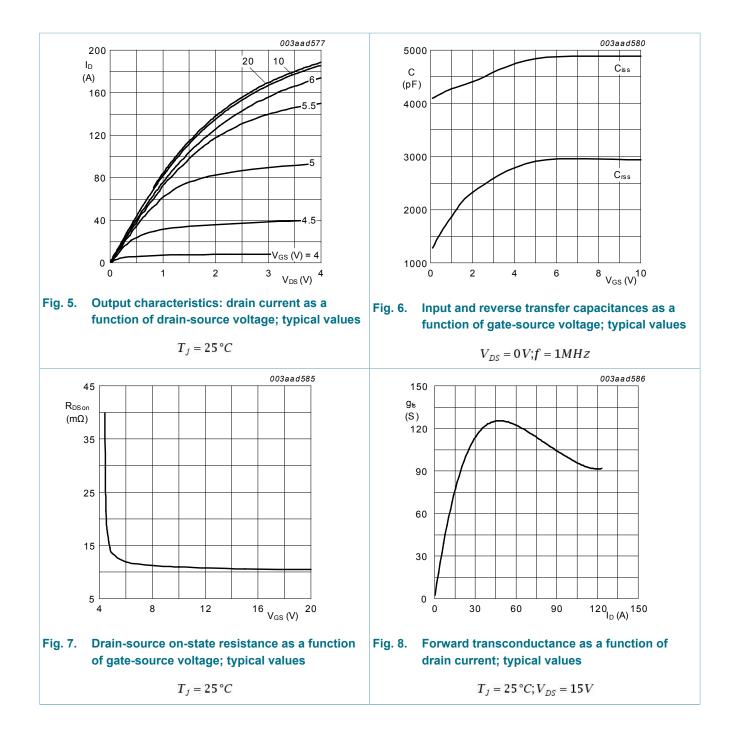
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| Symbol | Parameter | Conditions | | Min | Тур | Мах | Unit |
|---------------------------------------|---------------------------------------|--|-----|-----|------|------|------|
| | | V _{GS} = 10 V; I _D = 15 A; T _j = 175 °C; <u>Fig. 12</u> | | - | 29.5 | 38.9 | mΩ |
| | | V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 13</u> | [1] | - | 10.8 | 13.9 | mΩ |
| R _G | internal gate resistance (AC) | f = 1 MHz | | - | 1 | - | Ω |
| Dynamic ch | naracteristics | | | | | | |
| Q _{G(tot)} total gate charge | | I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; Fig. 14; Fig. 15 | | - | 59 | - | nC |
| | | I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V | | - | 47.6 | - | nC |
| Q _{GS} | gate-source charge | I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; Fig. 14; Fig. 15 | | - | 13.8 | - | nC |
| Q _{GS(th)} | pre-threshold gate- source charge | I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; Fig. 15 | | - | 9.2 | - | nC |
| $Q_{GS(th-pl)}$ | post-threshold gate- source charge | | | - | 4.6 | - | nC |
| Q _{GD} | gate-drain charge | I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; Fig. 15; Fig. 14 | | - | 17 | - | nC |
| V _{GS(pl)} | gate-source plateau voltage | V _{DS} = 50 V; <u>Fig. 15; Fig. 14</u> | | - | 4.4 | - | V |
| C _{iss} | input capacitance | V_{DS} = 50 V; V_{GS} = 0 V; f = 1 MHz; | | - | 3195 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C; <u>Fig. 16</u> | | - | 221 | - | pF |
| C _{rss} | reverse transfer capacitance | - | | - | 136 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 50 V; R_L = 2 Ω ; V_{GS} = 10 V; | | - | 20.7 | - | ns |
| t _r | rise time | R _{G(ext)} = 4.7 Ω; T _j = 25 °C | | - | 25 | - | ns |
| t _{d(off)} | turn-off delay time | | | - | 52.5 | - | ns |
| t _f | fall time | | | - | 24 | - | ns |
| Source-dra | in diode | 1 | 1 | | | | |
| V _{SD} | source-drain voltage | I_{S} = 15 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 17</u> | | - | 0.85 | 1.2 | V |
| t _{rr} | reverse recovery time | I_{S} = 25 A; dI _S /dt = 100 A/µs; V _{GS} = 0 V; | | - | 52 | - | ns |
| Qr | recovered charge | V _{DS} = 50 V | | - | 109 | - | nC |

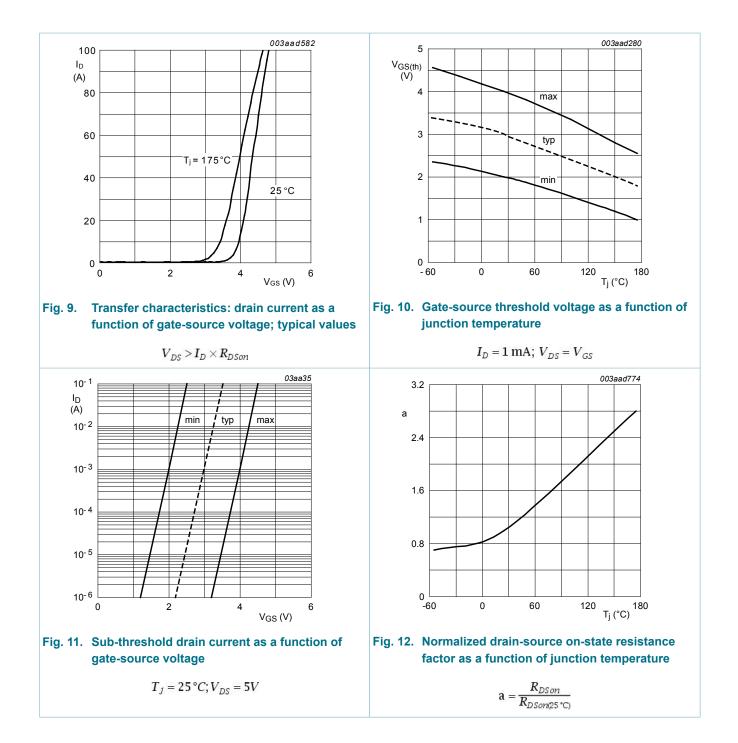
[1] Measured 3 mm from package.

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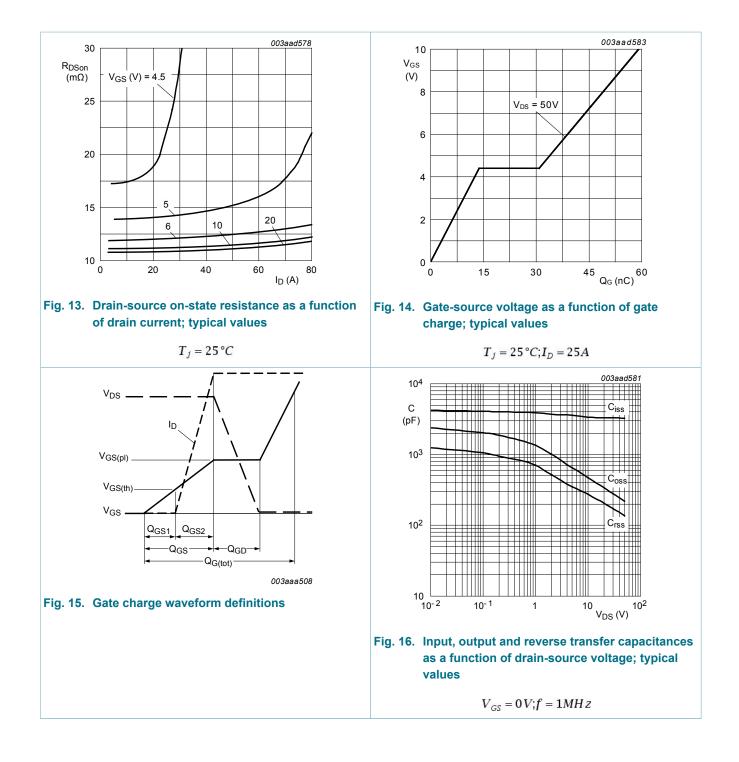


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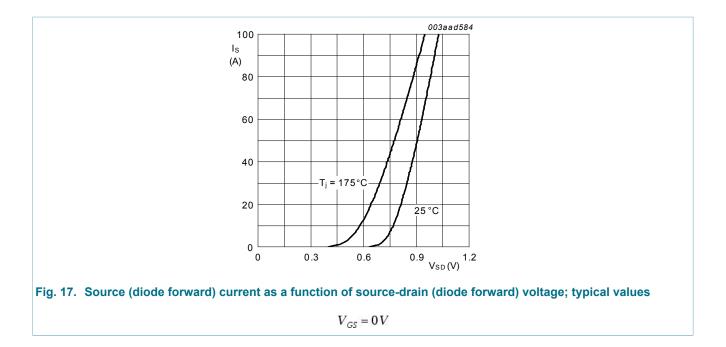
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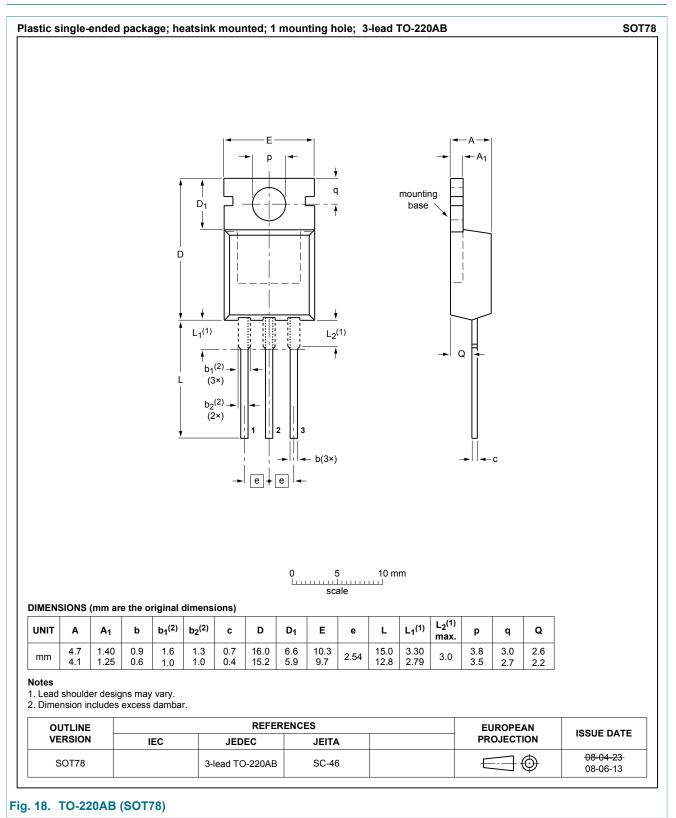
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8. Package outline



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9. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|-----------------------|---|
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